

Clean version of all pending claims:

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1. (Amended once) A transformer comprising:
 - a substrate comprising a semiconductor material;
 - a first conductor over the substrate, the first conductor defining a generally spiral-shaped signal path having at least one turn;
 - a second conductor over the substrate, the second conductor defining a generally spiral-shaped signal path having at least one turn; and
 - one, and no more than one, magnetic layer over the substrate.
2. The transformer of claim 1, wherein the magnetic layer comprises cobalt.
3. The transformer of claim 1, wherein the magnetic layer comprises an amorphous alloy comprising cobalt.
4. The transformer of claim 1, wherein the magnetic layer comprises an amorphous alloy comprising cobalt and zirconium.
5. The transformer of claim 1, wherein the magnetic layer comprises an amorphous alloy comprising cobalt; zirconium; and tantalum, niobium, or a rare earth element.
6. The transformer of claim 1, wherein the second conductor lies over the first conductor.

7. (Amended once) The transformer of claim 6, wherein the magnetic layer lies in a position selected from between the substrate and the first conductor, between the first and second conductors, and over the second conductor.

11. (Amended once) A transformer comprising:

a substrate comprising a semiconductor material;
a first conductor over the substrate, the first conductor defining a generally spiral-shaped signal path having at least one turn;
a second conductor over the substrate and over the second conductor and defining a generally spiral-shaped signal path having at least one turn; and
a magnetic layer disposed between all of the spiral-shaped signal path of the first conductor and all of the spiral-shaped signal path of the second conductor.

12. (Withdrawn from consideration) The transformer of claim 1, wherein the first and second conductors are positioned side-by-side.

13. (Withdrawn from consideration) The transformer of claim 12, wherein the first and second conductors each lie over the magnetic layer.

14. (Withdrawn from consideration) The transformer of claim 13, comprising another magnetic layer over the first and second conductors.

15. (Withdrawn from consideration) The transformer of claim 12, wherein the magnetic layer lies over the first and second conductors.

16. (Amended once) The transformer of claim 1, wherein the first and second conductors are positioned such that at least a portion of one or more turns of the first conductor are each positioned adjacent to an inner side of at least a portion of one turn of the second conductor and such that at least a portion of one or more turns of the second conductor are each positioned adjacent to an inner side of at least a portion of one turn of the first conductor.

17. The transformer of claim 16, wherein the first and second conductors each lie over the magnetic layer.

20. (Amended once) A method comprising:

forming a first conductor over a substrate comprising a semiconductor material, wherein the forming the first conductor comprises forming the first conductor such that the first conductor defines a generally spiral-shaped signal path having at least one turn;

forming a second conductor over the substrate such that the second conductor defines a generally spiral-shaped signal path having at least one turn; and

forming one and only one magnetic layer over the substrate.

21. The method of claim 20, wherein the forming the magnetic layer comprises forming a magnetic layer comprising cobalt.

22. The method of claim 20, wherein the forming the magnetic layer comprises forming a magnetic layer comprising an amorphous alloy comprising cobalt.

23. The method of claim 20, wherein the forming the magnetic layer comprises forming a magnetic layer comprising an amorphous alloy comprising cobalt and zirconium.

24. The method of claim 20, wherein the forming the magnetic layer comprises forming a magnetic layer comprising an amorphous alloy comprising cobalt; zirconium; and tantalum, niobium, or a rare earth element.

25. The method of claim 20, wherein the forming the second conductor comprises forming the second conductor over the first conductor.

26. (Amended once) The method of claim 25, wherein the forming the magnetic layer comprises forming the magnetic layer in a position selected from between the substrate and the first conductor, between the first and second conductors, and over the second conductor.

27-30. (Cancelled)

31. (Withdrawn from consideration) The method of claim 20, wherein the forming the first conductor and the forming the second conductor comprise forming the first and second conductors such that the first and second conductors are positioned side-by-side.

32. (Withdrawn from consideration) The method of claim 31, wherein the forming the first and second conductors comprises forming the first and second conductors over the magnetic layer.

33. (Withdrawn from consideration) The method of claim 32, comprising forming another magnetic layer over the first and second conductors.

34. (Withdrawn from consideration) The method of claim 31, wherein the forming the magnetic layer comprises forming the magnetic layer over the first and second conductors.

35. (Amended once) The method of claim 20, wherein the forming the first conductor and the forming the second conductor comprise forming the first and second conductors such that at least a portion of one or more turns of the first conductor are each positioned adjacent to an inner side of at least a portion of one turn of the second conductor and such that at least a portion of one or more turns of the second conductor are each positioned adjacent to an inner side of at least a portion of one turn of the first conductor.

36. The method of claim 35, wherein the forming the first and second conductors comprises forming the first and second conductors over the magnetic layer.

38. The method of claim 35, wherein the forming the magnetic layer comprises forming the magnetic layer over the first and second conductors.